

85. (Amended) The capacitor of claim 53, wherein the [metal] dielectric layer is formed from at least one metal selected from the group consisting of titanium, copper, gold, tungsten, and nickel.

107. (Amended) The capacitor of claim 19, wherein the oxide of the metal layer comprises titanium.

108. (Amended) The capacitor of claim 19, further comprising at least one of a diffusion barrier layer and an oxidation resistant layer interposed between the first conductive plate and the oxide of the metal layer.

109. (Amended) The memory system of claim 20, wherein the oxide of the metal layer comprises titanium.

110. (Amended) The memory system of claim 20, further comprising at least one of a diffusion barrier layer and an oxidation resistant layer interposed between the first conductive plate and the oxide of the metal layer.

111. (Amended) The capacitor of claim 53, wherein the [metal] dielectric layer comprises titanium.

112. (Amended) The capacitor of claim 53, further comprising at least one of a diffusion barrier layer and an oxidation resistant layer interposed between the first capacitor electrode and the [metal] dielectric layer.